#### Structure

Silicon N-channel MOSFET

#### Features

- 1) Low On-resistance.
- 2) 4V drive.

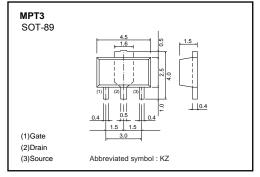
## Applications

Switching

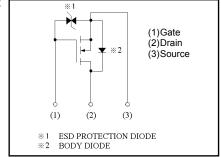
Packaging specifications

- r donaging opcomeducine				
	Package	Taping		
Type	Code	T100		
	Basic ordering unit (pieces)	1000		
RHP030N03		0		

## ●Dimensions (Unit : mm)



#### ●Inner circuit



## ●Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		$V_{DSS}$	30	V
Gate-source voltage		V <sub>GSS</sub>	±20	V
Danier account	Continuous	ID	3	Α
Drain current	Pulsed I <sub>DP</sub> *1		10	Α
Reverse drain current	Continuous	Idr	3	Α
reverse drain current	Pulsed	I <sub>DRP</sub> *1	10	Α
Total power dissipation		Ь	500	mW
		P <sub>D</sub>	2 *2	W
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	-55 to +150	°C

#### ●Thermal resistance

- 111011114111100101411100			
Parameter	Symbol	Limits	Unit
Channel to ambient	Bth(oh o)	250	°C/W
Channel to ambient	Rth(ch-a)	62.5 *	°C/W

<sup>\*</sup> When mounted on a 40×40×0.7mm ceramic board

<sup>\*1</sup> Pw≤10μs, Duty cycle≤1% \*2 When mounted on a 40×40×0.7mm ceramic board

**Data Sheet** 

## ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	I <sub>GSS</sub>	_	_	±10	μА	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V
Drain-source breakdown voltage	V <sub>(BR)</sub> DSS	30	_	_	V	I <sub>D</sub> = 1mA, V <sub>GS</sub> =0V
Zero gate voltage drain current	I <sub>DSS</sub>	_	-	1	μА	V <sub>DS</sub> = 30V, V <sub>GS</sub> =0V
Gate threshold voltage	V <sub>GS (th)</sub>	1.0	-	2.5	V	V <sub>DS</sub> = 10V, I <sub>D</sub> = 1mA
Static drain-source on-state resistance	R <sub>DS (on)</sub> *	_	90	120	mΩ	ID= 3A, VGS= 10V
		-	160	210	mΩ	I <sub>D</sub> = 3A, V <sub>GS</sub> = 4V
Forward transfer admittance	Y <sub>fs</sub>   *	2.0	-	_	S	V <sub>DS</sub> = 10V, I <sub>D</sub> = 3A
Input capacitance	Ciss	_	160	_	pF	V <sub>DS</sub> = 10V
Output capacitance	Coss	-	90	_	pF	V <sub>GS</sub> =0V
Reverse transfer capacitance	Crss	_	27	_	pF	f=1MHz
Turn-on delay time	<b>t</b> d (on) *	_	7	_	ns	V <sub>DD</sub> ≒ 15V
Rise time	tr *	_	11	_	ns	I <sub>D</sub> = 1.5A V <sub>G</sub> s= 10V
Turn-off delay time	t <sub>d (off)</sub> *	_	15	_	ns	VGS= 10V   RL=10Ω
Fall time	t <sub>f</sub> *	_	4.5	_	ns	R <sub>G</sub> =10Ω
Total gate charge	Qg *	_	6.5	_	nC	V <sub>DD</sub> ≒15V
Gate-source charge	Q <sub>gs</sub> *	-	1.0	-	nC	V <sub>GS</sub> = 10V
Gate-drain charge	Q <sub>gd</sub> *	_	1.5	_	nC	ID= 3A

<sup>\*</sup>Pulsed

#### •Electrical characteristics curves

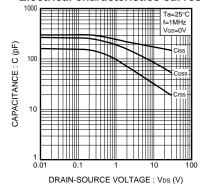


Fig.1 Typical Capacitance vs. Drain-Source Voltage

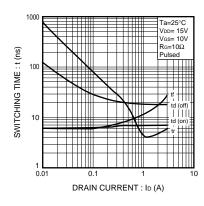


Fig.2 Switching Characteristics

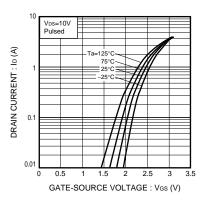


Fig.3 Typical Transfer Characteristics

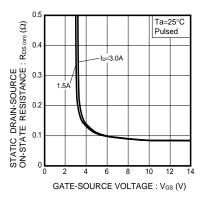


Fig.4 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

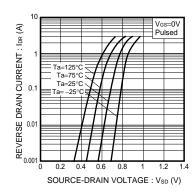


Fig.5 Reverse Drain Current vs. Source-Drain Voltage ( I )

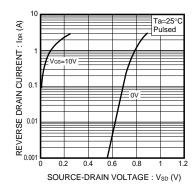


Fig.6 Reverse Drain Current vs. Source-Drain Voltage ( II )

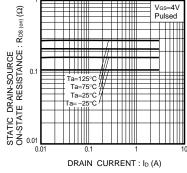


Fig.8 Static Drain-Source On-State Resistance vs. Drain Current ( II )

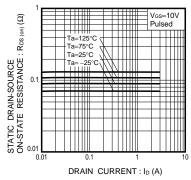


Fig.7 Static Drain-Source On-State Resistance vs. Drain Current ( I )

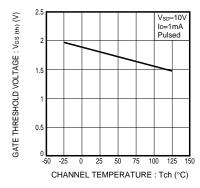


Fig.9 Gate Threshold Voltage vs. Channel Temperature

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